

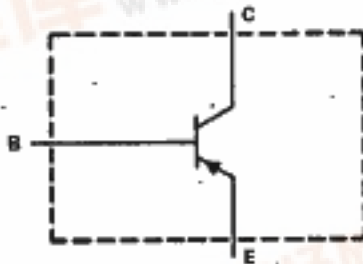
TIP74, TIP74A, TIP74B, TIP74C
P-N-P SILICON POWER TRANSISTORS

FEBRUARY 1977 — REVISED OCTOBER 1984

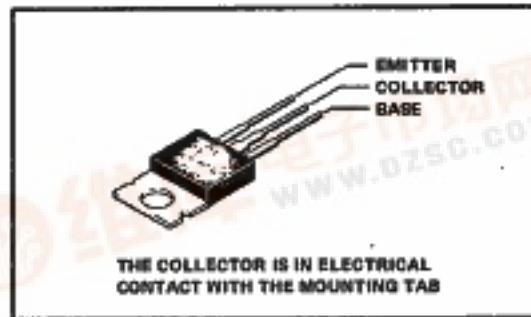
- Designed for Complementary Use with TIP73, TIP73A, TIP73B, TIP73C
- 80 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Min f_T of 5 MHz at 4 V, 1 A
- Meet or Surpass all JEDEC Registered Specifications for 2N6489, 2N6490, and 2N6491 at 25°C
- Designed for Power Amplifier and High-Speed Switching Applications

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device schematic



TO-220AB PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	TIP74	TIP74A	TIP74B	TIP74C
Collector-base voltage	-50 V	-70 V	-80 V	-110 V
Collector-emitter voltage ($I_B = 0$)	-40 V	-60 V	-80 V	-100 V
Emitter-base voltage	-5 V			
Continuous collector current	-15 A			
Continuous base current	-5 A			
Safe operating areas at (or below) 25°C case temperature	See Figure 9			
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)	80 W			
Continuous device dissipation at (or below) 25°C free-air temperature (see Note 2)	2 W			
Unclamped inductive load energy (see Note 3)	80 mJ			
Operating collector junction and storage temperature range	-65°C to 180°C			
Lead temperature 3.2 mm (0.126 inch) from case for 10 seconds	360°C			

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C or refer to Dissipation Derating Curve, Figure 10.
 2. Derate linearly to 150°C free-air temperature at the rate of 16 mW/°C or refer to Dissipation Derating Curve, Figure 11.
 3. This rating is based on the capability of the transistor to operate safely in the circuit of Figure 2. $L = 20$ mH, $R_{\theta B2} = 100 \Omega$, $V_{B2} = 0$ V, $R_B = 0.1 \Omega$, $V_{CC} = -20$ V. Energy = $I_C^2 L / 2$.

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 TIP Devices



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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TIP74			TIP74A			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
V_{BRICEO}	$I_C = -200 \text{ mA}$, $I_B = 0$, See Note 4	-40			-60			V
V_{BRICEV}	$I_C = -200 \text{ mA}$, $V_{BE} = 1.5 \text{ V}$, See Note 4	-80			-70			V
I_{CEO}	$V_{CE} = -30 \text{ V}$, $I_B = 0$			-50		-50		μA
I_{CES}	$V_{CE} = -40 \text{ V}$, $V_{BE} = 0$ $V_{CE} = -60 \text{ V}$, $V_{BE} = 0$			-50		-50		μA
I_{EBO}	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-50		-50		μA
h_{FE}	$V_{CE} = -4 \text{ V}$, $I_C = -5 \text{ A}$, See Notes 4 and 5 $V_{CE} = -4 \text{ V}$, $I_C = -15 \text{ A}$, See Notes 4 and 5	20		150	20		150	
V_{BE}	$V_{CE} = -4 \text{ V}$, $I_C = -5 \text{ A}$, See Notes 4 and 5 $V_{CE} = -4 \text{ V}$, $I_C = -15 \text{ A}$, See Notes 4 and 5			-1.3		-1.3		V
$V_{CE(sat)}$	$I_B = -500 \text{ mA}$, $I_C = -5 \text{ A}$, See Notes 4 and 5 $I_B = -5 \text{ A}$, $I_C = -15 \text{ A}$, See Notes 4 and 5			-1.3		-1.3		V
h_{fe}	$V_{CE} = -4 \text{ V}$, $I_C = -1 \text{ A}$, $f = 1 \text{ kHz}$	25			25			
f_{β}	$V_{CE} = -4 \text{ V}$, $I_C = -1 \text{ A}$, $f = 1 \text{ MHz}$	5			5			

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TIP74B			TIP74C			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
V_{BRICEO}	$I_C = -200 \text{ mA}$, $I_B = 0$, See Note 4	-80			-100			V
V_{BRICEV}	$I_C = -200 \text{ mA}$, $I_B = 0$, See Note 4	-90			-110			V
I_{CEO}	$V_{CE} = -60 \text{ V}$, $I_B = 0$			-50		-50		μA
I_{CES}	$V_{CE} = -80 \text{ V}$, $V_{BE} = 0$ $V_{CE} = -100 \text{ V}$, $V_{BE} = 0$			-50		-50		μA
I_{EBO}	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-50		-50		μA
h_{FE}	$V_{CE} = -4 \text{ V}$, $I_C = -5 \text{ A}$, See Notes 4 and 5 $V_{CE} = -4 \text{ V}$, $I_C = -15 \text{ A}$, See Notes 4 and 5	20		150	20		150	
V_{BE}	$V_{CE} = -4 \text{ V}$, $I_C = -5 \text{ A}$, See Notes 4 and 5 $V_{CE} = -4 \text{ V}$, $I_C = -15 \text{ A}$, See Notes 4 and 5			-1.3		-1.3		V
$V_{CE(sat)}$	$I_B = -500 \text{ mA}$, $I_C = -5 \text{ A}$, See Notes 4 and 5 $I_B = -5 \text{ A}$, $I_C = -15 \text{ A}$, See Notes 4 and 5			-1.3		-1.3		V
h_{fe}	$V_{CE} = -4 \text{ V}$, $I_C = -1 \text{ A}$, $f = 1 \text{ kHz}$	25			25			
f_{β}	$V_{CE} = -4 \text{ V}$, $I_C = -1 \text{ A}$, $f = 1 \text{ MHz}$	5			5			

- NOTES: 4. These parameters must be measured using pulse techniques, $t_W = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
5. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm (0.125 inch) from the device body.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$			1.56	$^{\circ}\text{C/W}$
$R_{\theta JA}$			62.5	$^{\circ}\text{C/W}$
$R_{\theta CHS}$ (see Note 6)			0.7	$^{\circ}\text{C/W}$
$C_{\theta C}$			0.9	$\text{J}/^{\circ}\text{C}$

NOTE 6: This parameter is measured using 0.08 mm (0.003 inch) mica insulator with Dow-Corning 11 compound on both sides of the insulator, a 0.138-32 (formerly 6-32) mounting screw with bushing, and a mounting torque of 0.9 newton-meter (8 inch-pounds).

TIP Devices

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P-N-P SILICON POWER TRANSISTORS

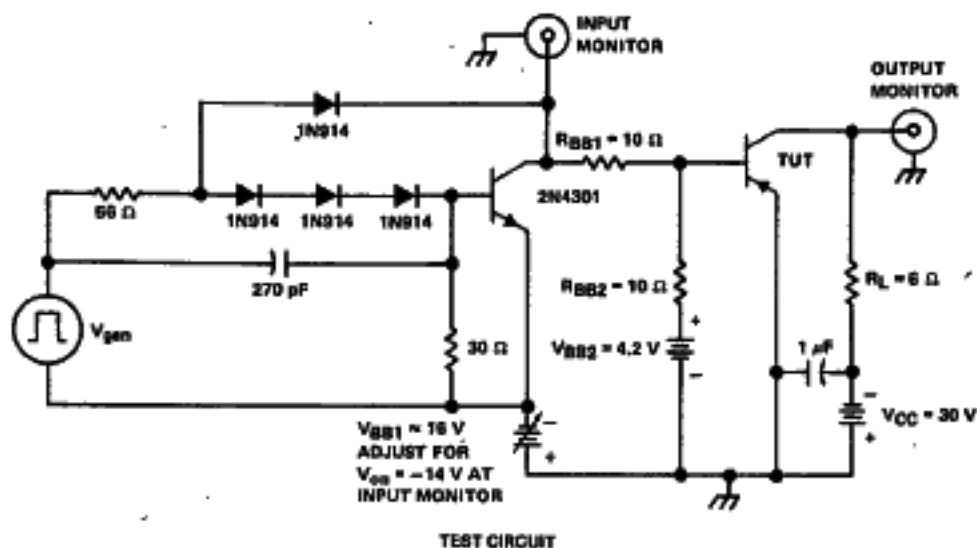
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resistive-load switching characteristics at 25°C case temperature (unless otherwise noted)

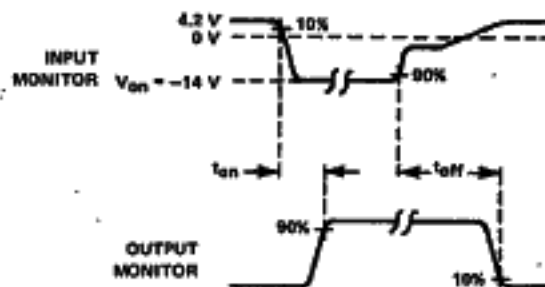
PARAMETER	TEST CONDITIONS†	MIN	TYP	MAX	UNIT
t_d	$I_C = -5A, I_{B1} = -0.5A, I_{B2} = 0.5A,$ $V_{BE(off)} = 4.2V, R_L = 6\Omega,$ See Figure 1		20		ns
t_r			120		ns
t_s			600		ns
t_f			300		ns

†Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

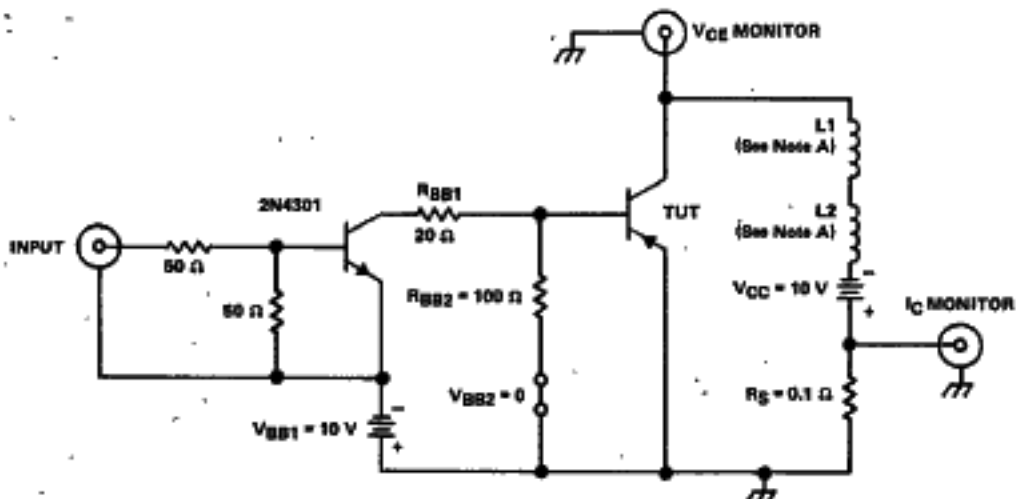
- NOTES:
- V_{gen} is a 30-V pulse into a 50 Ω termination.
 - The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r < 15$ ns, $t_f < 15$ ns, $Z_{out} = 50 \Omega$, $t_{pw} = 20 \mu s$, duty cycle $\leq 2\%$.
 - Waveforms are monitored on an oscilloscope with the following characteristics: $t_r < 15$ ns, $R_{in} > 10$ M Ω , $C_{in} < 11.5$ pF.
 - Resistors must be noninductive types.
 - The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING

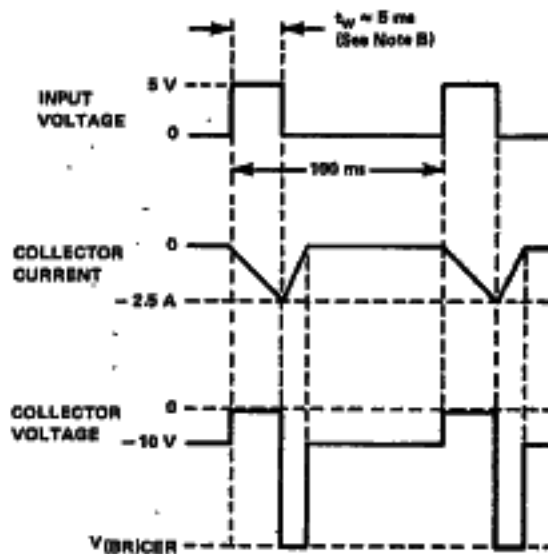
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PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

NOTES: A. L1 and L2 are 10 mH, 0.11 Ω , Chicago Standard Transformer Corporation C-2688, or equivalent.
B. Input pulse duration is increased until $I_{CM} = -3$ A.

FIGURE 2. INDUCTIVE-LOAD SWITCHING

TIP Devices

TYPICAL CHARACTERISTICS

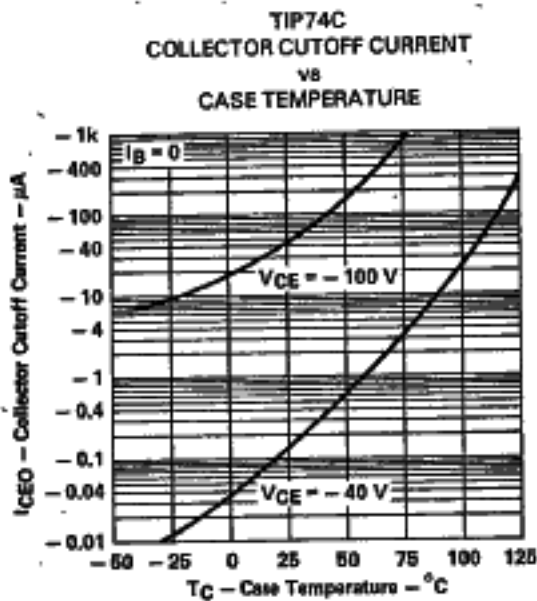


FIGURE 3

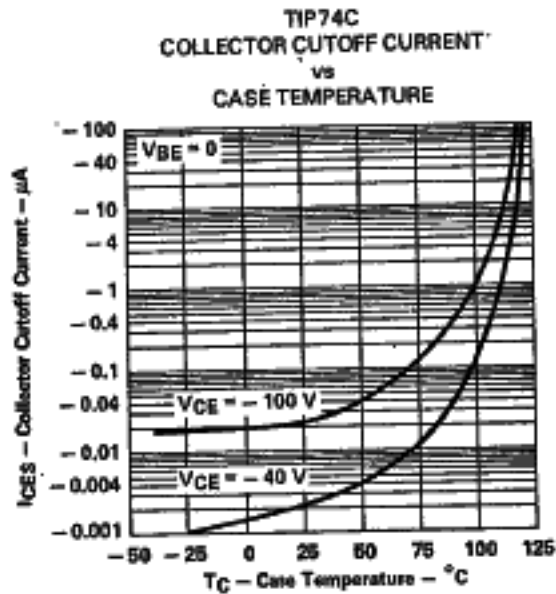


FIGURE 4

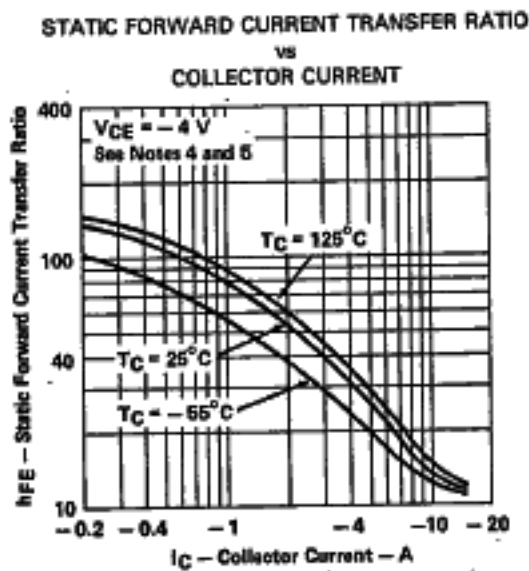


FIGURE 5

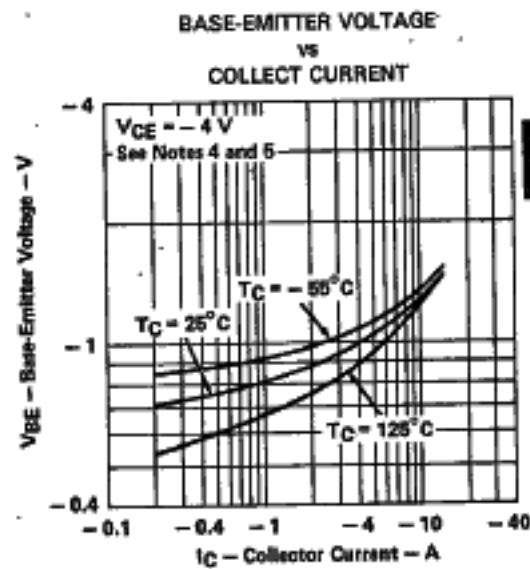


FIGURE 6

- NOTES: 4. These parameters must be measured using pulse techniques, $t_W = 300 \mu s$, duty cycle $< 2\%$.
5. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm (0.125 inch) from the device body.

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TYPICAL CHARACTERISTICS

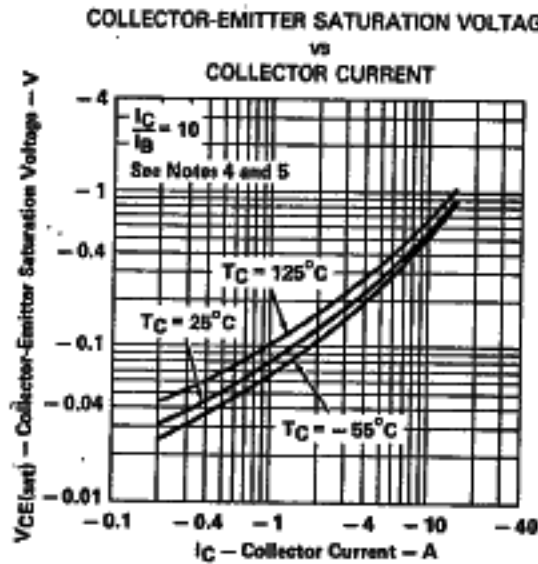


FIGURE 7

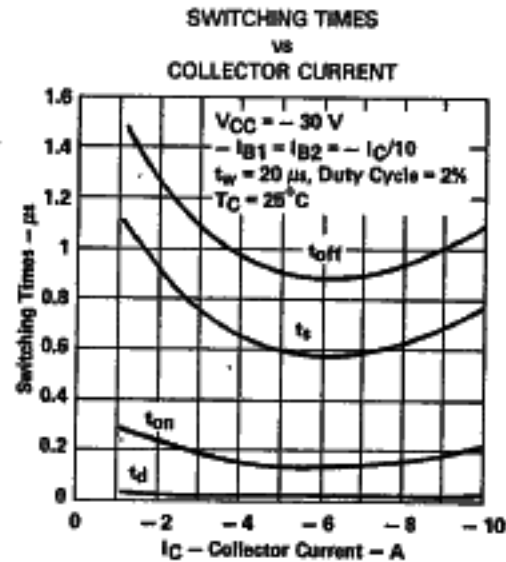


FIGURE 8

- NOTES: 4. These parameters must be measured using pulse techniques, $t_w = 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
5. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm (0.125 inch) from the device body.

MAXIMUM SAFE OPERATING AREA

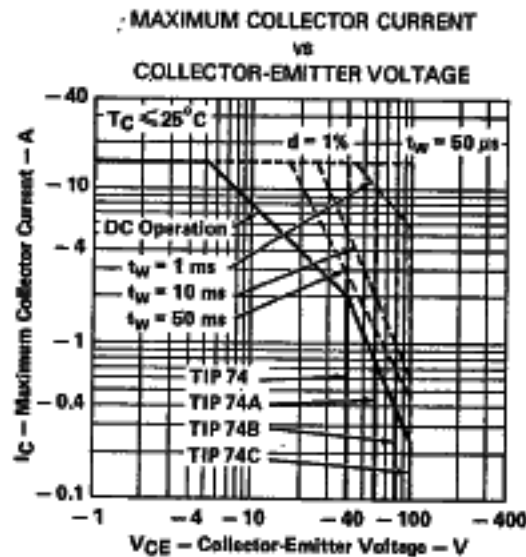


FIGURE 9

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THERMAL INFORMATION

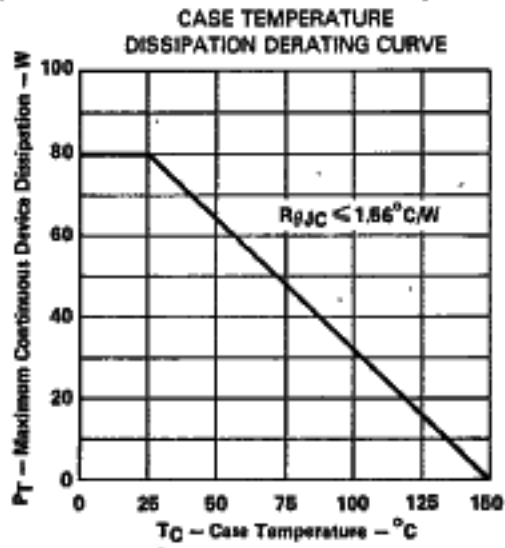


FIGURE 10

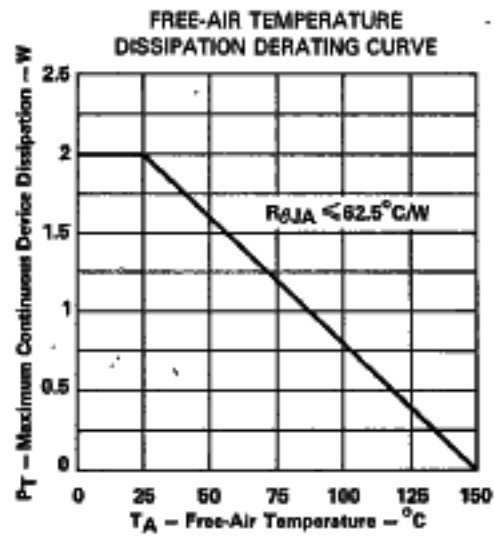


FIGURE 11



TIP Devices